

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

## 2SA1293

HIGH CURRENT SWITCHING APPLICATIONS.

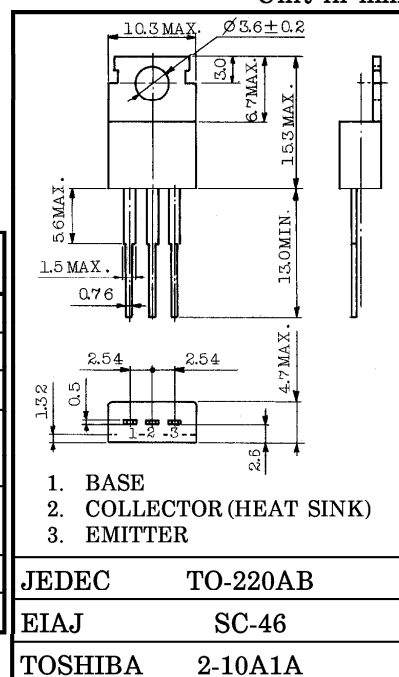
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = -0.4V$  (Max.) at  $I_C = -3A$
- High Speed Switching Time :  $t_{stg} = 1.0\mu s$  (Typ.)
- Complementary to 2SC3258.

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

| CHARACTERISTIC                                        |       | SYMBOL    | RATING  | UNIT       |
|-------------------------------------------------------|-------|-----------|---------|------------|
| Collector-Base Voltage                                |       | $V_{CBO}$ | -100    | V          |
| Collector-Emitter Voltage                             |       | $V_{CEO}$ | -80     | V          |
| Emitter-Base Voltage                                  |       | $V_{EBO}$ | -7      | V          |
| Collector Current                                     | DC    | $I_C$     | -5      | A          |
|                                                       | Pulse | $I_{CP}$  | -8      |            |
| Collector Power Dissipation<br>( $T_c = 25^\circ C$ ) |       | $P_C$     | 30      | W          |
| Junction Temperature                                  |       | $T_j$     | 150     | $^\circ C$ |
| Storage Temperature Range                             |       | $T_{stg}$ | -55~150 | $^\circ C$ |



Mounting Kit No. AC75

Weight : 1.9g

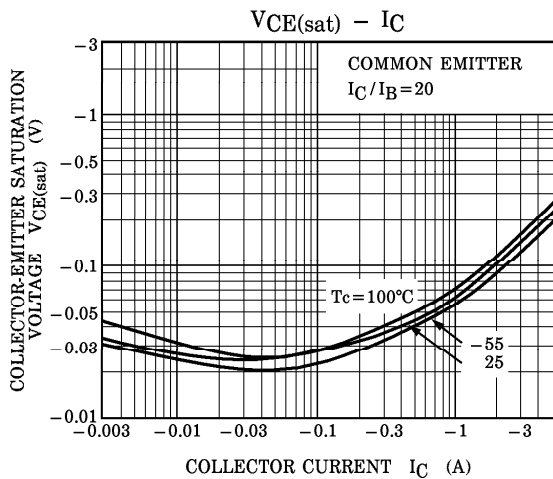
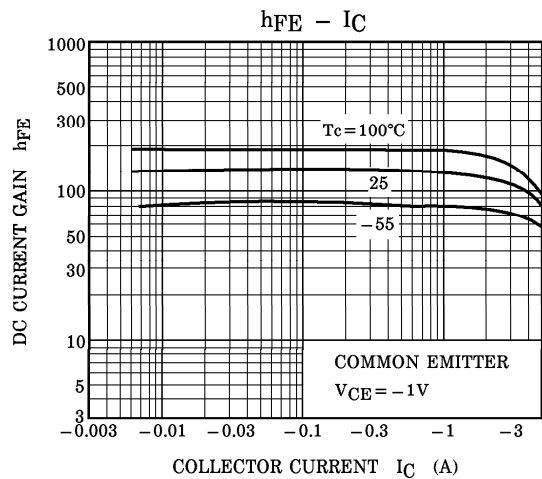
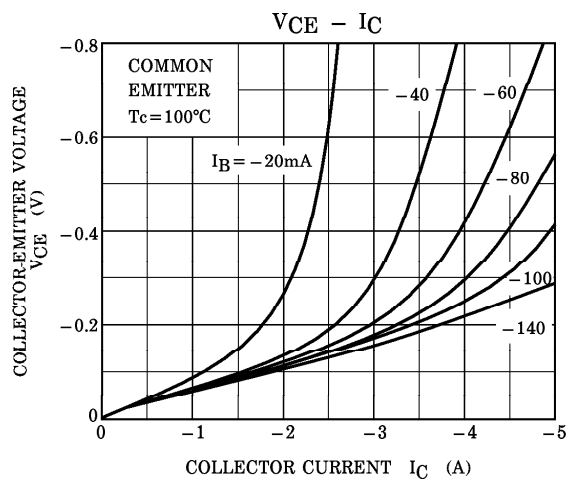
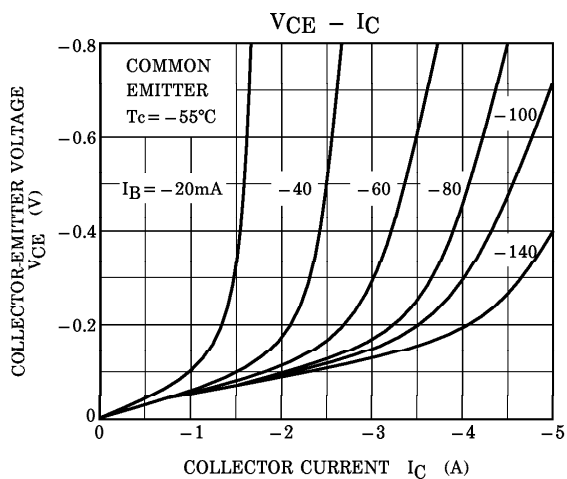
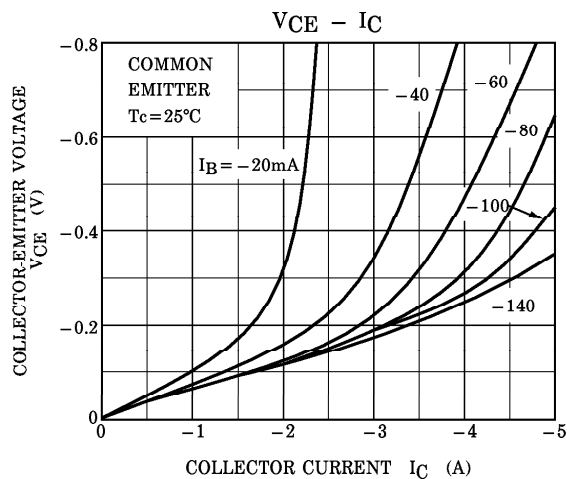
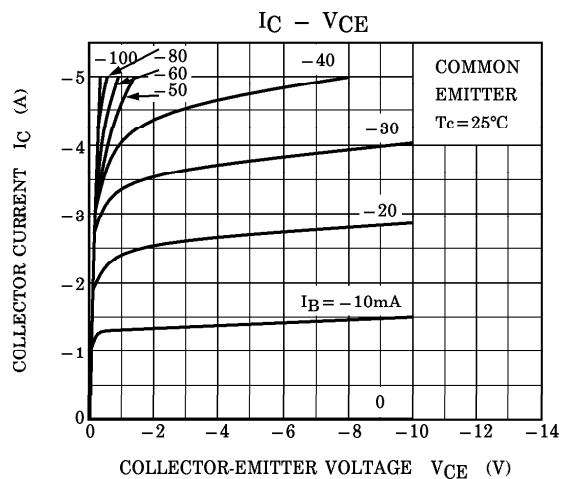
ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

| CHARACTERISTIC                      |                   | SYMBOL                | TEST CONDITION                     | MIN. | TYP. | MAX. | UNIT    |
|-------------------------------------|-------------------|-----------------------|------------------------------------|------|------|------|---------|
| Collector Cut-off Current           |                   | $I_{CBO}$             | $V_{CB} = -100V, I_E = 0$          | —    | —    | -1   | $\mu A$ |
| Emitter Cut-off Current             |                   | $I_{EBO}$             | $V_{EB} = -7V, I_C = 0$            | —    | —    | -1   | $\mu A$ |
| Collector-Emitter Breakdown Voltage |                   | $V_{(BR)CEO}$         | $I_C = -10mA, I_B = 0$             | -80  | —    | —    | V       |
| DC Current Gain                     |                   | $h_{FE(1)}$<br>(Note) | $V_{CE} = -1V, I_C = -1A$          | 70   | —    | 240  |         |
|                                     |                   | $h_{FE(2)}$           | $V_{CE} = -1V, I_C = -3A$          | 30   | —    | —    |         |
| Saturation Voltage                  | Collector-Emitter | $V_{CE(sat)}$         | $I_C = -3A, I_B = -0.15A$          | —    | -0.2 | -0.4 | V       |
|                                     | Base-Emitter      | $V_{BE(sat)}$         | $I_C = -3A, I_B = -0.15A$          | —    | -0.9 | -1.2 |         |
| Transition Frequency                |                   | $f_T$                 | $V_{CE} = -4V, I_C = -1A$          | —    | 60   | —    | MHz     |
| Collector Output Capacitance        |                   | $C_{ob}$              | $V_{CB} = -10V, I_E = 0, f = 1MHz$ | —    | 200  | —    | pF      |
| Switching Time                      | Turn-on Time      | $t_{on}$              |                                    | —    | 0.2  | —    | $\mu s$ |
|                                     | Storage Time      | $t_{stg}$             |                                    | —    | 1.0  | —    |         |
|                                     | Fall Time         | $t_f$                 |                                    | —    | 0.1  | —    |         |

Note :  $h_{FE(1)}$  Classification O : 70~140, Y : 120~240

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